# Index


**a**

adiabatic compression phenomenon 323
AFM multiprobe application 284
AlGaN/GaN heterostructures
  contacts 166, 168
  dielectrics for gate insulated AlGaN/GaN transistors 169, 170, 171
  electrical nanocharacterization 168, 169
  graphene contacts 178–180
  local electrical properties of graphene 2DEG 173–175
  Schottky barrier and resistivity in $MoS_2$ 175–178
amplitude modulation technique (AM-mode) 299
ANSCM-PT probe 274
As-deposited amorphous $HfO_2$ dielectric 120
As-doped homojunction ZnO nanorods 306
atomic force microscope (AFM) 1–4
atomic layer deposited (ALD) $HfO_2$ film 109
"Au-free" metal stacks 165
Au nanoparticles (NPs) 301
Au/n-type GaAs nano junction 335

**b**

bi-layer (BL) GeSi QDs 149
bipolar junction transistor (BJT) 244
Bruker DTRCH-AM holder 86

**c**

Cabrera–Mott theory 216
capacitance–voltage ($C$–$V$) technique 79
CHC-stressed MOSFETs 229
classical electromagnetic model (EM) 329
coating of probes 32–34
conductive atomic force microscope (CAFM) 264–267
  atomic layer deposited $HfO_2$ films 11
  cantilever choice 36
  coating of probes 32–34
  conductive thin film probes 34–35
  constant voltage stress 81
  corner tips 31
  data acquisition 7
  dielectric breakdown 80
  different fields of science 11, 12
  displacement currents 85–89
  electrical wear 39, 40
  etched silicon probes 31
  energy conversion potential of ZnO nanowires 19
  Faraday cage 4
  GaN/InGaN nanowires arrays 16
  GeSi quantum dots (QDs), *see* GeSi quantum dots (QDs)
  GeSi quantum rings (QRs), *see* GeSi quantum rings (QRs)
  grain boundaries in polycrystalline films 80
  high-k dielectric films, *see* high-k dielectric films


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conductive atomic force microscope (CAFM) (*contd.*)
  hysteretic bipolar switching phenomenon 15
  interfacial SiO2 thickness 94–98
  *I*–*V* curve 9
  Kaiser Holoprobe Raman instrument 15
  lateral resolution of the technique 5
  leakage current conduction mechanisms 80
  *vs.* macroscopic *I*–*V* measurements 81–85
  material conversion 35
  mechanical wear-different materials 39
  mechanical wear-varying forces 38–39
  morphology of thin dielectric films 89–93
  nanowires 16–20
  n-type ZnO NWs 18
  photolithography 11
  piezoelectric NW arrays 16
  post deposition annealing 80
  ramped voltage stresses 8
  resolution of C-AFM tips 37–38
  research 12, 13
  sample surface damage 42–43
  $SiO_2$ films 10
  standard silicon nanoprobes 6
  structure 4
  thin film cantilever 30
  tip damage by excess voltage/high currents 40–42
  tip material choice 36–37
  tip/sample systems 5
  trapping phenomena and degradation mechanism in high-k dielectric stacks 98–104
  typical low noise preamplifier 7
  unprecedented high resolution and topography-current correlation 10
  vapor-liquid-solid process 17
  Veeco DI 3100 AFM 12
  vertically aligned ZnO nanowires 16
conductive thin film probes 34
conductive-bridge random access memory (CBRAM) 196
constant current stress (CCS) 226
constant voltage stress (CVS) 226
corner tips 31
CyroView MP™ multiprobe cryogenic system 289

***d***

DD-FORTA probe 273
defects in SiC after plasma exposure in fusion reactors 64, 65
Derjaguin–Muller–Toporov (DMT) model 53
dielectric breakdown induced epitaxy (DBIE) 231
dip-pen nanolithography[8,9] (DPN) 211
Dual Match Pair Transistor HFA3134 245

***e***

electrical conductivity of dislocations in GaN 67, 68
electrochemical metallization cells (EMC) 196
extended TUNA module 82

***f***

field effect transistors (FETs) 307
fifty Hz notch filter 248
filamentary-based resistive switching cells (ReRAMs) 196
force-assisted AFM nanolithography 211
Fowler–Nordheim tunnelling (FNT) 55, 84, 144
frequency modulation technique (FM-mode) 299
full diamond AFM probe 34
full diamond tips (FDT) 193

***g***

GaN/InGaN nanowires arrays 16
gate oxide reliability 104–108
GeSi quantum dots (QDs)
  applications in electronics and optoelectronics 134
  bias voltage 146–149

electrical property 137–140
growth conditions 135
growth temperature dependence 135, 136
inter-dot coupling 149–152
oxidation and normal force 144, 145, 146
physical properties 134
GeSi quantum rings (QRs)
conductive mechanism 140–144
electrical characteristics 134
measurements of composition and current distributions 152, 154
nano-electronic devices 134
persistent current and A-B effects 134
graphene
C buffer layer 172
electrostatic phenomenon 175
isolation of 171
local electrical and structural in homogeneities 172
local electrical properties of 173–175
scalable synthesis approaches 171

### h
hafnium based oxides 84
Hertz contact theory 47
Hewlet Packard semiconductors analyzer HP4145B 254
$HfO_2/SiO_x$ dielectric stack 120–124
$HfSi_xO_y$ grains and grain boundaries 90
high electron mobility transistors (HEMTs) 164
high Q factor probes 282
high-k dielectric films
bimodal TDDB distributions 109–112
gate oxide reliability 104–108
highest occupied molecular orbital (HOMO) 301
hot electron mapping 336–338
hot electron nanoscopy and spectroscopy (HENs)
coupling schemes 321–325
fast pulses 347, 348
hot electron mapping 336–338
hot electron resolution limit 338–339
plasmonic device and optical characterization 326–327
quantum confinement 334–335
quantum mechanical considerations 333–334
semiclassical considerations 329–333
sensitivity and specificity 344–346
SKPM theoretical frame 340–343
spatial resolution 344, 345
hot electron resolution limit 338, 339
HP4145B semiconductors analyzer 254

### i
input current 248
InSb nanodots 302, 303
internal photoemission (IPE) 335

### j
junctions and heterostructrues, KPFM 305, 307

### k
Kaiser Holoprobe Raman instrument 15
Kelvin probe force microscope (KPFM) 58, 292
AM and FM-mode 299–300
basic principle 297–299
ITO substrates 311
junctions and heterostructrues 305–307
measurement 300–301
metallic nanostructures 301–302
organic adsorbates on surfaces 304–305
semiconductor surfaces 302–304
solar cells 308–311
structural and electronic properties 311
transistors 307–308
UV photo-emission spectroscopy 311

### l


laser-sintered
  Ge nanoparticles 46
  nanoparticles 69, 70
LM394 Dual Match Pair Transistor 252
local anodic oxidation (LAO)
  current-controlled 219
  kinetics 214–216
  measurement of electrical current 217–219
  schematic of 212, 213
  silicon carbide 213
  time-resolved photoemission spectroscopy 213
LogAmpDev00 252
LogAmpDev02 252
LogAmpDev05 252
LogAmpDev06 252
LogAmpDev07 252, 255, 256
logarithmic converter block (LCB) 245, 246
logarithmic $I$–$V$ converter 259
logarithmic preamplifier
  block diagram 244
  cleaning 250
  decoupling 250–251
  design 244–246,249
  differential amplifier gain 253
  digital circuitry 251
  Hewlet Packard semiconductors analyzer HP4145B 254
  implementation in CAFM 255–260
  input and output isolation 251
  instrumentation set-up 254
  $I$–$V$ response curve 253
  LogAmpDev00 252
  LogAmpDev02 252
  LogAmpDev05 252
  LogAmpDev06 252
  LogAmpDev07 252
  printed circuit board 249–250
  R4-C1 network 254
  ResiScope 261
  Soft ResiScope modes 261
  unexpected Passive components in the PCB 251–255
  voltage source units (VSU) 254
low pass filter 248
lowest unoccupied molecular orbital (LUMO) 301


### m


macroscopic current–voltage ($I$–$V$) technique 79
many-body perturbation theory (MBPT) 333
material conversion 35
metal coated probes 32
metal–insulator–semiconductor (MIS)/metal–insulator–metal gate stacks 79
metal/semiconductor Schottky barrier 168
metallic nanostructures 301, 302
Mg doped GaN nanorods 305
microelectromechanical systems (MEMS) 30
multiprobe atomic force microscopy (AFM) 277
multiprobe graphene nanoribbon conductivity measurements 291
multiprobe platform
  AFM multiprobe application 284–285
  feedback of multiprobe systems 282–284
  measurements 291–292
  nanoelectrical transport measurements 287–290
  optical multiprobe operation 285
  probes 281–282
  scanner 279–281
  thermal measurements 285–287
multi-spectroscopies scanning probe apparatus 320
MultiView 4000™ MultiProbe SPM 281


### n


Nanonics Flat Scanner™ 280
Nanonics Imaging MultiView 4000™ MultiProbe SPM System 278

Nanonics MultiView 4000 system 279
NANOSENSORS™ PPPEFM100 86
NanoToolKit™ 281, 291
nanowires (NWs) 16
near-field scanning optical microscopy (NSOM) 278, 279
non-inverting summing amplifier 248
nonstressed MOSFETs 229
n-type ZnO NWs 18

*o*

one-dimensional Schottky Barrier (SB) model 335
operational amplifier (OPAMP) 244
operation modes, CAFM
  bias voltage 45, 46
  contact mode 61, 62
  defects in SiC after plasma exposure in fusion reactors 64, 65, 67
  electrical conductivity of dislocations in GaN 67, 68
  Hertz contact theory 47
  laser-sintered Ge nanoparticles 46
  laser-sintered nanoparticles 69, 70
  metal-coated silicon tip 48
  PeakForce Mode 62, 63
  tip on insulating surfaces 52–56
  tip on metallic surfaces 49, 50
  tip on semiconducting surfaces 50, 51, 52
  torsional resonance mode 61, 63–64
  work function difference and offset voltage 56–60
optical multiprobe operation 285
oxide resistive random access memory (OxRRAM) 197

*p*

PeakForce CAFM (PF CAFM) 62
PeakForce TUNA 62
phenyl-C61-butyric acid methyl ester (PCBM) 310
photonic crystal (PhC) 323
piezoelectric NW arrays 16
platinum silicide AFM probe 35
poly [(9,9-bis(3′-(*N*,*N*-dimethylamino) propyl)-2,7-fluorene)-alt-2,7-(9,9-dioctylfluorene)] (PFN) 304
polycrystalline $HfO_2$ dielectrics
  degradation and breakdown 119
  experimental details and sample specifications 120, 121
  formation of grain boundaries and local electrical properties 120, 122, 124
  RVS and CVS stressing 124–127
  uniform stressing, CAFM 126–129
poly(3-hexylthiophene) (P3HT)/$TiO_2$ nanorod solar cells 306
polypyrrole-hyaluronic acid (PPy-HA) 305
Pool–Frenkel (PF) emission mechanism 170
position sensitive detector (PSD) 283
pristine $MoS_2$ nanoflakes 302
Pt/Ir
  coated probes 82
  coated tips 65
  EFM probes 86
pump probe near-field scanning optical microscopy (NSOM) 278

*q*

quantum confinement effects 133
quantum corral 212
quantum point contact model 49
quasiparticle self-consistent GW (QSGW) scheme 333

*r*

ramped voltage stress (RVS) 8, 226
rapid thermal oxidation (RTO) 168
reference current 248
ResiScope
  actual current 269
  advantages 269, 270
  current/resistance spectroscopy mode 270, 271
  electric measurements 270
  local resistance 267, 268
  schematics 267, 268

resistive random access memories (RRAM) 230
resistive switching analyses
- device level stress 230, 235
- direct connection 235, 237

### s

scalpel SPM
- chemical nature 202–203
- depth information 188–190
- description 190–193
- failure analysis, 203–206
- limitations 207
- mechanisms for filament growth 200–202
- practical implementation 193–196
- 3D observation of conductive filaments in resistive memories 196–200

scanning Auger microscopy (SAM) 139
scanning capacitance microscopy (SCM) 29, 80
scanning Kelvin probe microscopy (SKPM) 340, 343
scanning probe lithography(SPL) 211, 212
scanning probe microscopy (SPM) 188, 319
- tomography work-flow 192

scanning spreading resistance microscopy (SSRM) 29, 62
scanning tunneling microscopy (STM) 277
Schottky Au-GaAs junction 321
Schottky emission 50
self-assembled GeSi QDs 137
self-assembled monolayers (SAMs) 213
semiconductor parameter analyzer (SPA) 226, *see also* SPA/CAFM combination
- probestation setup 227
- ramped voltage stress 227
- ultra-low noise tri-axial cables 226

semiconductor surfaces 302, 304
Si nanowires (NWs) 308
- transistors 213, 214

signal-to-noise ratio (SNR) 243
silicon carbide (SiC) 64
single-layer (SL) GeSi QDs 149
$SiO_2$ films 10
$SiO_2$-oligothiophene 307
$SiO_x$ interfacial layer (IL) 109
soft electrical materials 274
soft Resiscope mode
- ANSCM-PT probe 274
- DD-FORTA probe 273
- fast point contact at constant force 272
- intermittent contact mode 272
- intrinsic disadvantages of contact mode 271
- linear regime 271
- PMMA polymer blend sample 273
- sinusoidal regime 271, 272
- soft electrical materials 274

solar cells 308, 311
SPA/CAFM combination
- device level stress 230–235
- direct connection 235–237
- local channel hot carriers degradation analysis 227–230

spin-orbit (SO) coupling 333
standard silicon nanoprobes 6
sub-diffraction optical probe 320
surface plasmon polaritons (SPPs) 327
- quantum mechanical nature of 320

### t

3D observation of conductive filaments in resistive memories 196
thin film cantilever 30
thin film solar cells 308
time-dependent dielectric breakdown (TDDB) 109
$TiN/HfO_2/Pt$ MIM structures 232
TiO2 MIM structures 81
TiO2(TiCl4) 81
TiO2(TTIP) 81
tip-induced material removal 192
tip speed 195

tomogram formation and 3D reconstruction 196
torsional resonance conductive atomic force microscopy (TR CAFM) 61, 63
transimpedance amplifier (TIA) 336
transistors 307, 308
trap-assisted tunneling 122
tuning fork probe 283
tunneling AFM (TUNA) 29, 80
two dimensional electron gas (2DEG) 163
typical low noise preamplifier 7

*u*
unstressed pMOSFET transistors 228

*v*
valence change memory (VCM) 196
Veeco DI 3100 AFM 12
Veeco Dimension 5000 SPM system 82
vertically aligned ZnO nanowires 16

*w*
wear resistant diamond tip 193

*z*
ZnO photocatalysts 301